

FDG361N

N-Channel 100V Specified PowerTrench® MOSFET

General Description

These N-Channel 100V specified MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain low gate charge for superior switching performance.

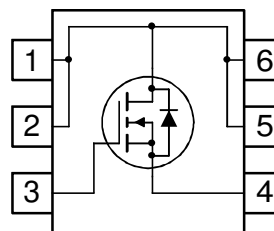
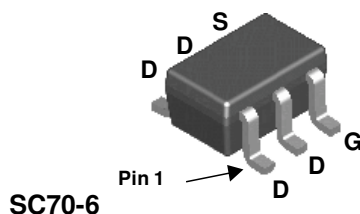
These devices have been designed to offer exceptional power dissipation in a very small footprint for applications where the bigger more expensive SO-8 and TSSOP-8 packages are impractical.

Applications

- Load switch
- Battery protection
- Power management

Features

- 0.6 A, 100 V. $R_{DS(ON)} = 500 \text{ m}\Omega @ V_{GS} = 10 \text{ V}$
 $R_{DS(ON)} = 550 \text{ m}\Omega @ V_{GS} = 6.0 \text{ V}$
- Low gate charge (3.7nC typical)
- Fast switching speed
- High performance trench technology for extremely low $R_{DS(ON)}$



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter	Rated	Units
V _{DSS}	Drain-Source Voltage	100	V
V _{GSS}	Gate-Source Voltage	±20	V
I _D	Drain Current – Continuous (Note 1a)	0.6	A
	– Pulsed	2.0	
P _D	Power Dissipation for Single Operation (Note 1a) (Note 1b)	0.42	W
		0.38	
T _J , T _{STG}	Operating and Storage Junction Temperature Range	–55 to +150	°C

Thermal Characteristics

R _{θJA}	Thermal Resistance, Junction-to-Ambient (Note 1a)	300	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient (Note 1b)	333	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
.61	FDG361N	7"	8mm	3000 units

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C		105		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}$			10	μA
I_{GSSF}	Gate–Body Leakage, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			100	nA
I_{GSSR}	Gate–Body Leakage, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$			-100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2	2.6	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C		-5		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = 10\text{ V}, I_D = 0.6\text{ A}$ $V_{GS} = 6\text{ V}, I_D = 0.6\text{ A}$ $V_{GS} = 10\text{ V}, I_D = 0.6\text{ A}, T_J = 125^\circ\text{C}$		370 396 685	500 550 976	m Ω
$I_{D(on)}$	On–State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 10\text{ V}$	2			A
g_{FS}	Forward Transconductance	$V_{DS} = 5\text{ V}, I_D = 0.6\text{ A}$		3.6		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V},$		153		pF
C_{oss}	Output Capacitance	$f = 1.0\text{ MHz}$		5		pF
C_{rss}	Reverse Transfer Capacitance			1		pF
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = 50\text{ V}, I_D = 1\text{ A},$		8	16	ns
t_r	Turn–On Rise Time	$V_{GS} = 10\text{ V}, R_{GEN} = 6\ \Omega$		4	8	ns
$t_{d(off)}$	Turn–Off Delay Time			11	20	ns
t_f	Turn–Off Fall Time			6	12	ns
Q_g	Total Gate Charge	$V_{DS} = 50\text{ V}, I_D = 0.6\text{ A},$		3.7	5	nC
Q_{gs}	Gate–Source Charge	$V_{GS} = 10\text{ V}$		0.8		nC
Q_{gd}	Gate–Drain Charge			1		nC
Drain–Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain–Source Diode Forward Current				0.4	A
V_{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 0.4\text{ A}$ (Note 2)		0.8	1.2	V

Notes:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



- a) 300°C/W when mounted on a 1 in^2 pad of 2 oz copper.



- b) 333°C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < $300\ \mu\text{s}$, Duty Cycle < 2.0%

Typical Characteristics

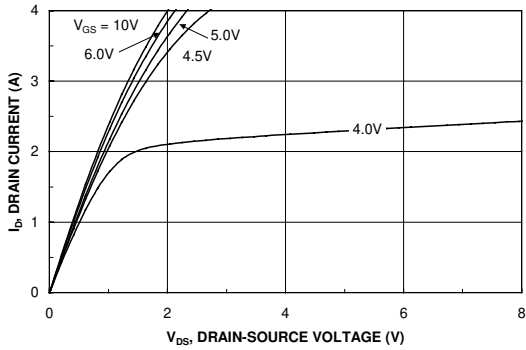


Figure 1. On-Region Characteristics.

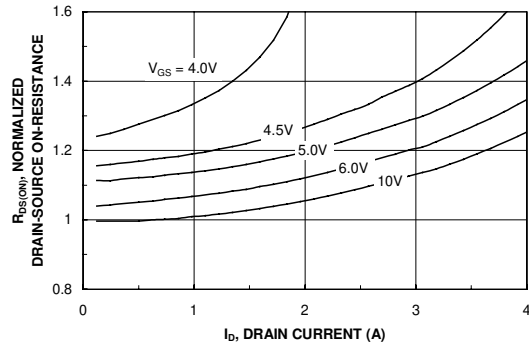


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

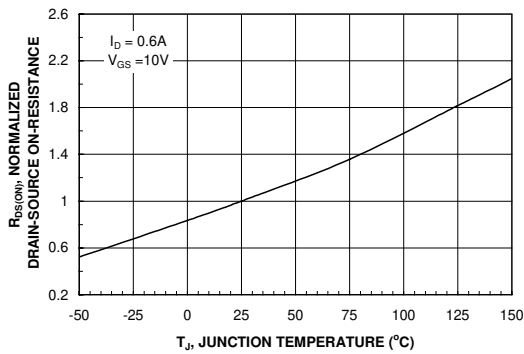


Figure 3. On-Resistance Variation with Temperature.

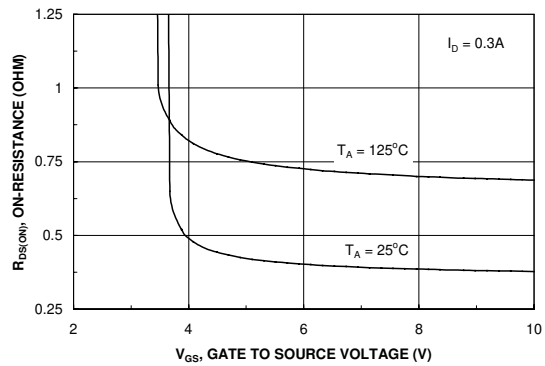


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

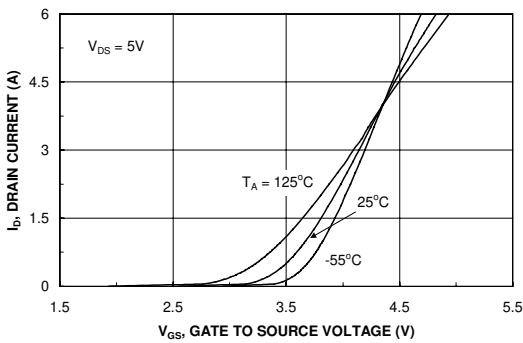


Figure 5. Transfer Characteristics.

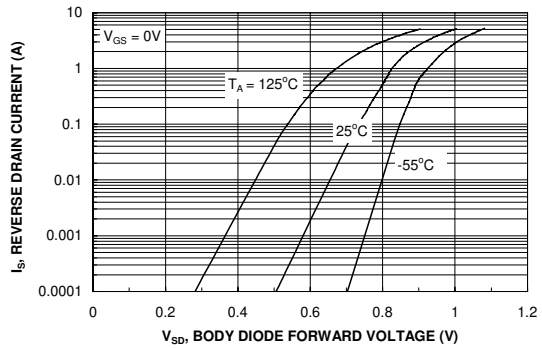


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

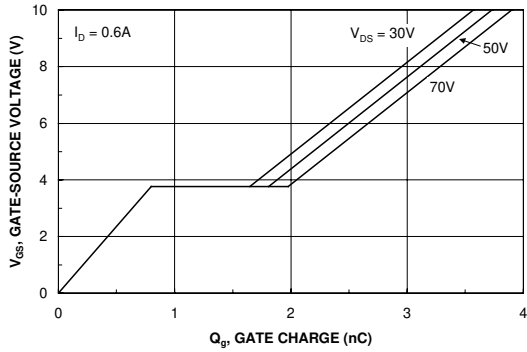


Figure 7. Gate Charge Characteristics.

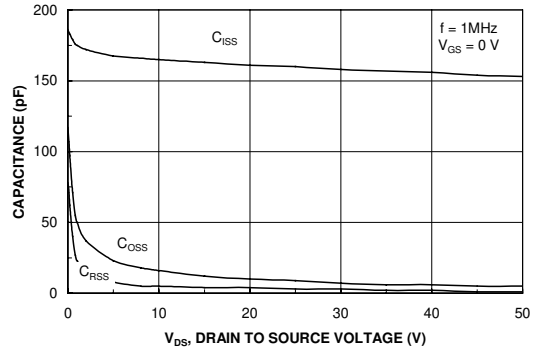


Figure 8. Capacitance Characteristics.

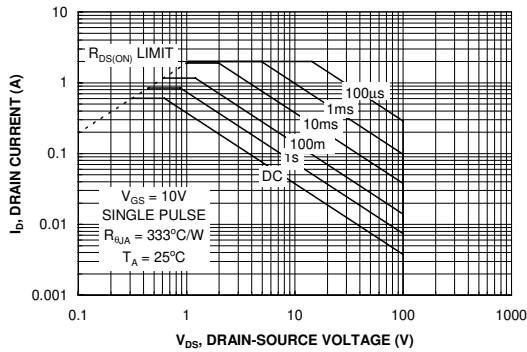


Figure 9. Maximum Safe Operating Area.

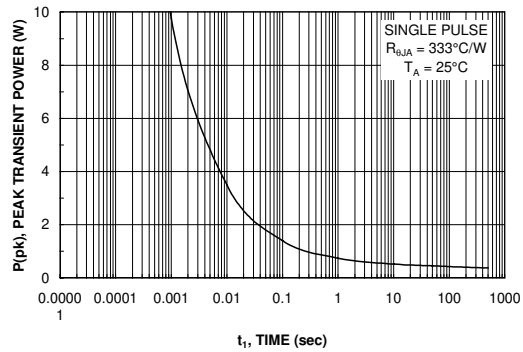


Figure 10. Single Pulse Maximum Power Dissipation.

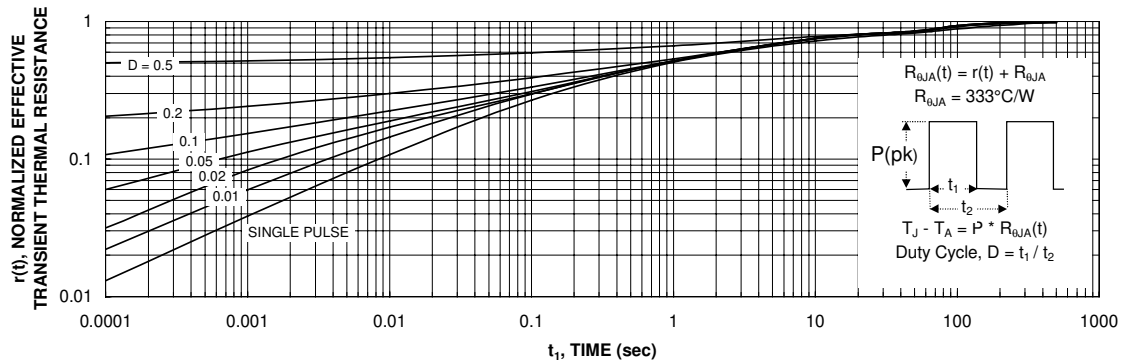


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

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